








 	<h2>RQ3E070BNTB</h2>
	<p>Hersteller-Teilenummer: RQ3E070BNTB</p> <p>Hersteller / Marke: LAPIS Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 7A HSMT8</p> <p>Datenblätter:  RQ3E070BNTB.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 2707 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	RQ3E070BNTB
Hersteller	LAPIS Semiconductor
Beschreibung	MOSFET N-CH 30V 7A HSMT8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	2707 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	150 °C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-PowerVDFN
Supplier Device-Gehäuse	8-HSMT (3.2x3)
Verlustleistung (max)	2W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	7A (Ta)
Rds On (Max) @ Id, Vgs	27 mOhm @ 7A, 10V
VGS (th) (Max) @ Id	2.5V @ 1mA
Gate Charge (Qg) (Max) @ Vgs	8.9nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	410pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Original-Reel®



















































RQ3E070BNTB ist neu im Original, Suche RQ3E070BNTB Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie RQ3E070BNTB LAPIS Semiconductor mit Garantie und Vertrauen. Anfrage RQ3E070BNTB: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>RQ3E075ATTB LAPIS Semiconductor PCH -30V -18A MIDDLE POWER MOSFE</p>	 <p>RQ3E080BN QQ2850920316 RQ3E080BN QQ2850920316</p>	 <p>RQ3E080BNFU7TB ROHM RQ3E080BNFU7TB ROHM</p>	 <p>RQ3C150BCTB LAPIS Semiconductor PCH -20V -30A MIDDLE POWER MOSFE</p>
 <p>RQ3E080BNFU7 LAPIS Semiconductor RQ3E080BNFU7 ROHM/</p>	 <p>RQ3E070BNFU7TB ROHM RQ3E070BNFU7TB ROHM</p>	 <p>RQ3E070BN QQ2850920 RQ3E070BN QQ2850920</p>	 <p>RQ3E080BNTB LAPIS Semiconductor MOSFET N-CH 30V 8A HSMT8</p>

heiße Teile

Mehr

 ADC08351CILQ	 BR24L04FVM-WTR	 GJM1555C1H7R9WB01D	 LP2981A-29DBVR	 LT1460JCS3-2.5#TRPBF
 MAX3075EESA	 MAX5741EUB+	 RQ3E070BN	 RQ3E070BNFU7	 RQ3E070BNFU7TB
 RQ3E080BN	 RQ3E080BNFU7	 RQ3E080BNFU7TB	 RQ3E080BNTB	 RQ3E080GN
 RQ3E080GNTB	 RQ3E100BN	 RQ3E100BNFU7	 RQ3E100BNFU7TB	 RQ3E100BNTB1
 RQ3E100GN	 RQ3E100GNFU7TB	 RQ3E100GNTB	 RQ3E100MN	 RQ3E100MNFU
 RQ3E100MNTB	 RQ3E110AJ	 RQ3E120AT	 RQ3E120AT-TB	 RQ3E120BN
 RQ3E120BNFU7TB	 RQ3E120GN	 RQ3E120GNTB	 RQ3E130BN	 RQ3E130BNFU7TB
 RQ3E130MNTB	 RQ3E130MUTB	 RQ3E13BNFU7	 RQ3E150BN	 RQ3E150BNFU7
 RQ3E150GN	 RQ3E150MN	 RQ3E150MNFU7TB1	 RQ3E150MNTB	 RQ3E160AD
 RQ3E160ADM6	 RQ3E160ADTB1	 RQ3E180BN	 RQ3E180GN	 RQ3G100GN

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited